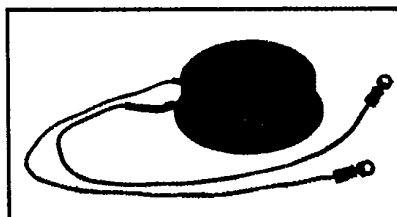
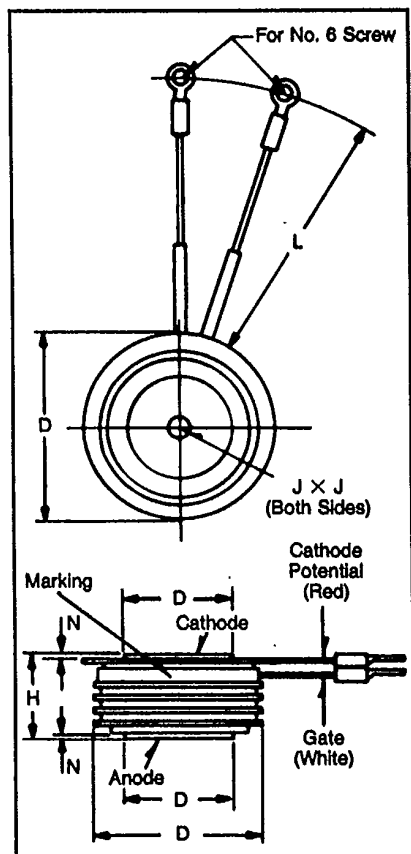


**T9G0**

Powerex, Inc. Hillis Street, Youngwood, Pennsylvania 15697 (412) 925-7272

Powerex Europe, S.A., 428 Ave. G. Durand, BP107, 72003 LeMans, France (43) 72.75.15

Phase Control SCR**1000-1200 Amperes Avg
100-2200 Volts**

T9G0
Phase Control SCR
1000-1200 Amperes/100-2200 Volts

Description

Powerex Silicon Controlled Rectifiers (SCR) are designed for phase control applications. These are all-diffused, Press-Pak (Pow-R-Disc) devices employing the field-proven amplifying (di/namic) gate.

Features:

- ☐ Low On-State Voltage
- ☐ High di/dt
- ☐ High dv/dt
- ☐ Hermetic Packaging
- ☐ Excellent Surge and I²t Ratings

Applications:

- ☐ Power Supplies
- ☐ Battery Chargers
- ☐ Motor Control
- ☐ Light Dimmers
- ☐ VAR Generators

Ordering Information

Example: Select the complete eight digit part number you desire from the table -- i.e. T9G01210 is a 1200 Volt, 1000 Ampere Phase Control SCR.

Type	Voltage		Current	
	V _{onm} V _{anm}	Code	I _r (avg)	Code
T9G0	100	01	1000	10
	200	02	1200	12
	400	04		
	600	06		
	800	08		
	1000	10		
	1200	12		
	1400	14		
	1600	16		
	1800	18		
	2000	20		
	2200	22		

T9G
Outline Drawing

Dimensions	Inches		Millimeters	
	Min.	Max.	Min.	Max.
φD	2.850	2.900	72.39	73.66
φD ₁	1.845	1.855	46.86	47.12
φD ₂	2.560	2.640	65.02	67.06
H	1.03	1.07	26.16	27.18
φJ	.135	.145	3.43	3.68
J ₁	.075	.090	1.91	2.29
L	11.50	12.50	292.10	317.50
N	.050	—	1.27	—

Creep Distance—1.20 in. min. (30.48 mm)

Strike Distance—.70 in. min. (17.78 mm).

(In accordance with NEMA standards.)

Finish—Nickel Plate.

Approx. Weight—1 lb. (454 g).

1. Dimension "H" is a clamped dimension.



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Absolute Maximum Ratings

	Symbol	T9G0 _ _ 10	T9G0 _ _ 12	Units
RMS On-State Current	$I_{T(RMS)}$	1590	1880	Amperes
Average On-State Current	$I_{T(av)}$	1000	1200	Amperes
Peak One-Cycle Surge (Non-Repetitive) On-State Current (60Hz)®	I_{TSM}	17,000	27,000	Amperes
Peak One-Cycle Surge (Non-Repetitive) On-State Current (50Hz)®	I_{TSM}	15,500	24,650	Amperes
Critical Rate-of-Rise of On-State Current (Non-Repetitive)® ① ②	di/dt	300	300	Amperes/ μ s
Critical Rate-of-Rise of On-State Current (Repetitive)	di/dt	150	150	Amperes/ μ s
I^2t (for Fusing), One Cycle at 60Hz	I^2t	1,203,000	3,040,000	A ² sec
Peak Gate Power Dissipation	P_{GM}	16	16	Watts
Average Gate Power Dissipation	$P_{G(av)}$	3	3	Watts
Storage Temperature	T_{STG}	-40 to 150	-40 to 150	°C
Operating Temperature	T_J	-40 to 125	-40 to 125	°C
Mounting Force®		5000 to 5500	5000 to 5500	lb.
Mounting Force®		2270 to 2500	2270 to 2500	kg

Electrical and Thermal Characteristics

	Symbol	Test Conditions	T9G0 _ _ 10	T9G0 _ _ 12	Units
Current—Conducting State Maximums					
Peak On-State Voltage	V_{TM}	$I_{TM} = 1500A, T_J = 25^\circ C$	1.75	1.35	Volts
Voltage—Blocking State Maximums®					
T9G0					
Forward Leakage, Peak	I_{DRM}	$T_J = 125^\circ C, V_{DRM} = \text{rated}$	75		mA
Reverse Leakage, Peak	I_{RRM}	$T_J = 125^\circ C, V_{RRM} = \text{rated}$	75		mA
Switching					
Typical Turn-Off Time	t_q	$I_T = 250A, T_J = 125^\circ C,$ $di_R/dt = 50A/\mu\text{sec},$ reapplied $dv/dt = 20V/\mu\text{sec}$ linear to $0.8V_{DRM}$	350		μsec
Typical Turn-On Time®	t_{on}	$I_{TM} = 1000A, V_D = 450V$	3		μsec
Min. Critical dv/dt exponential to V_{DRM} ® ③	dv/dt	$T_J = 125^\circ C$	300		V/ μsec
Thermal					
Maximum Thermal Resistance,® double sided cooling Junction to Case	$R_{\theta JC}$		.023		°C/Watt
Case to Sink, Lubricated	$R_{\theta CS}$		.0075		°C/Watt
Gate—Maximum Parameters					
Gate Current to Trigger	I_{GT}	$T_J = 25^\circ C, V_D = 12V$	200		mA
Gate Voltage to Trigger	V_{GT}	$T_J = 25^\circ C, V_D = 12V$	3.0		Volts
Non-Triggering Gate Voltage	V_{GDM}	$T_J = 125^\circ C, \text{rated } V_{DRM}$	.15		Volts
Peak Forward Gate Current	I_{GTM}		4		Amperes
Peak Reverse Gate Voltage	V_{GRM}		5		Volts

① Consult recommended mounting procedures.

② Applies for zero or negative gate bias.

③ Per JEDEC RS-397, 5.2.2.1.

④ With recommended gate drive.

⑤ Higher dv/dt ratings available, consult factory.

⑥ Per JEDEC standard RS-397, 5.2.2.6.



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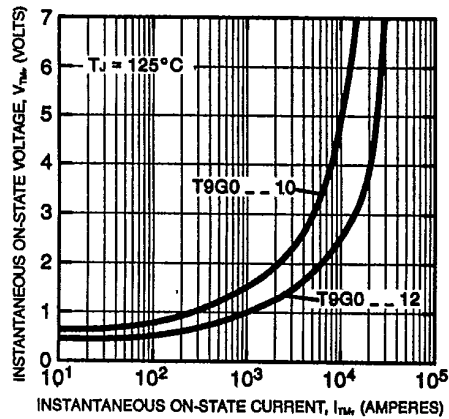
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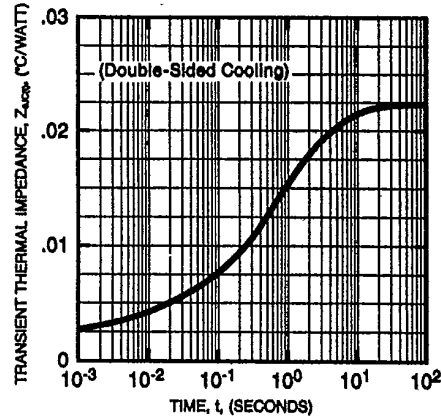
Phase Control SCR

1000-1200 Amperes Avg/100-2200 Volts

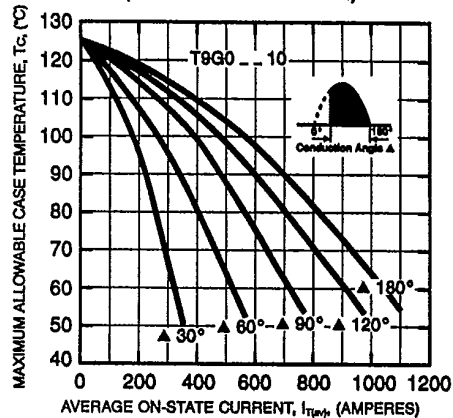
MAXIMUM ON-STATE CHARACTERISTICS



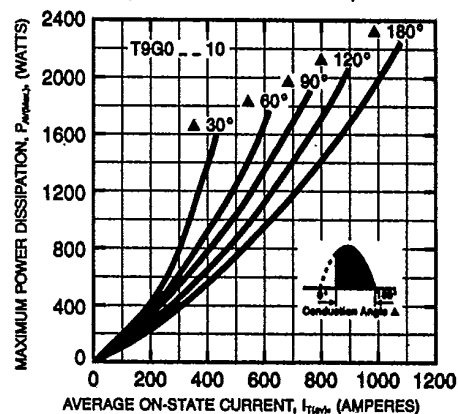
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)



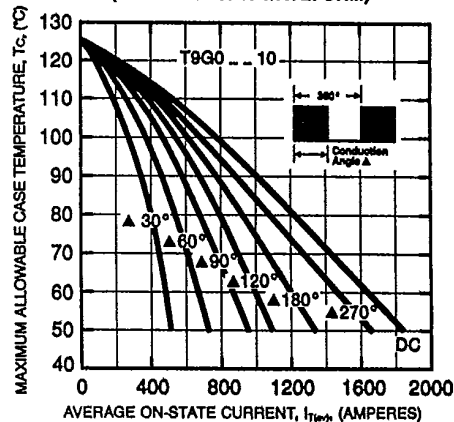
MAXIMUM ALLOWABLE CASE TEMPERATURE (SINUSOIDAL WAVEFORM)



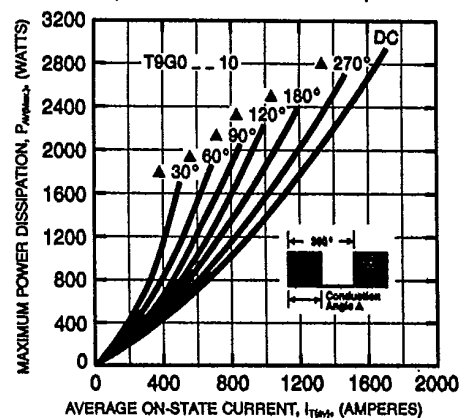
MAXIMUM ON-STATE POWER DISSIPATION (SINUSOIDAL WAVEFORM)



MAXIMUM ALLOWABLE CASE TEMPERATURE (RECTANGULAR WAVEFORM)



MAXIMUM ON-STATE POWER DISSIPATION (RECTANGULAR WAVEFORM)





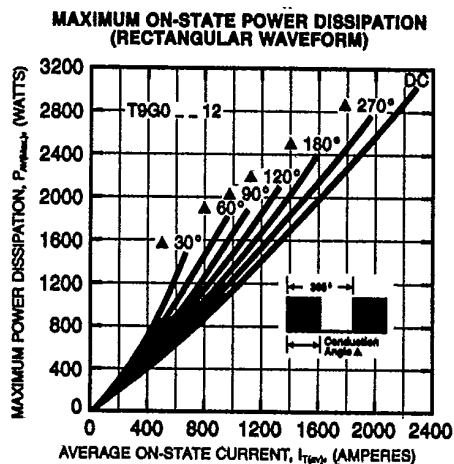
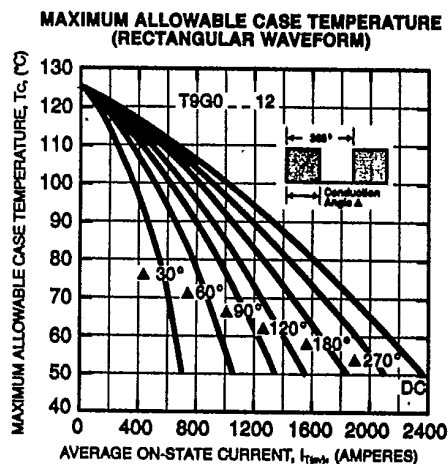
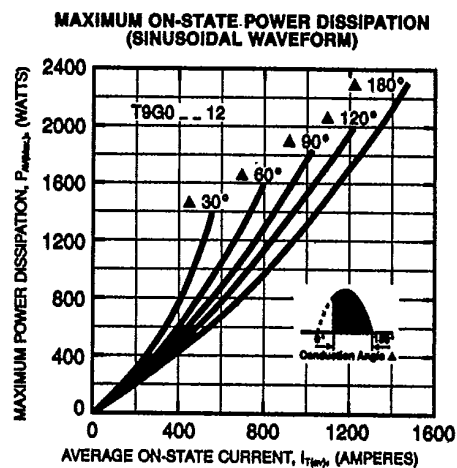
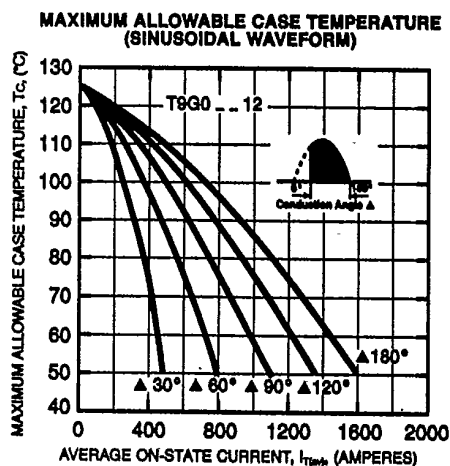
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Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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